

**INTRODUCE:**

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

**FEATURES:**

1. Avalanche characteristic.
2. Medium current, low forward voltage.
3. High frequency, Fast recovery.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

**APPLICATIONS:**

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. X-ray power supply.

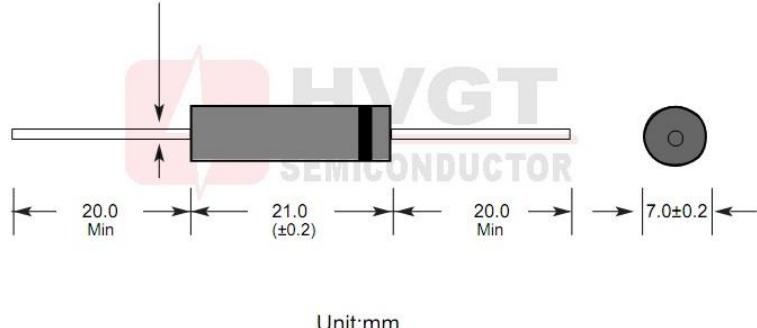
**MECHANICAL DATA:**

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.1 grams (approx).

**SHAPE DISPLAY:**

**SIZE: (Unit:mm)**
**HVGT NAME: DO-721**
**DO-721 Series**

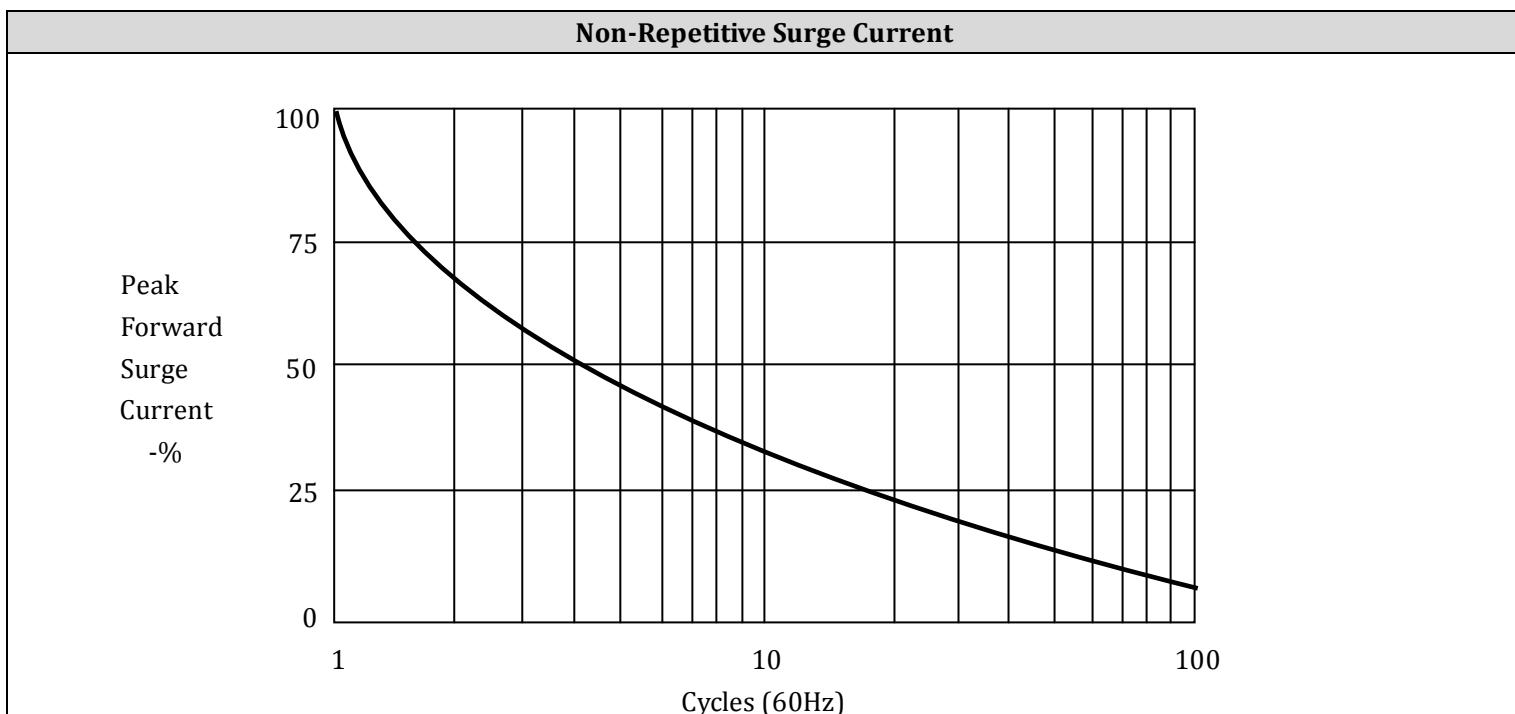
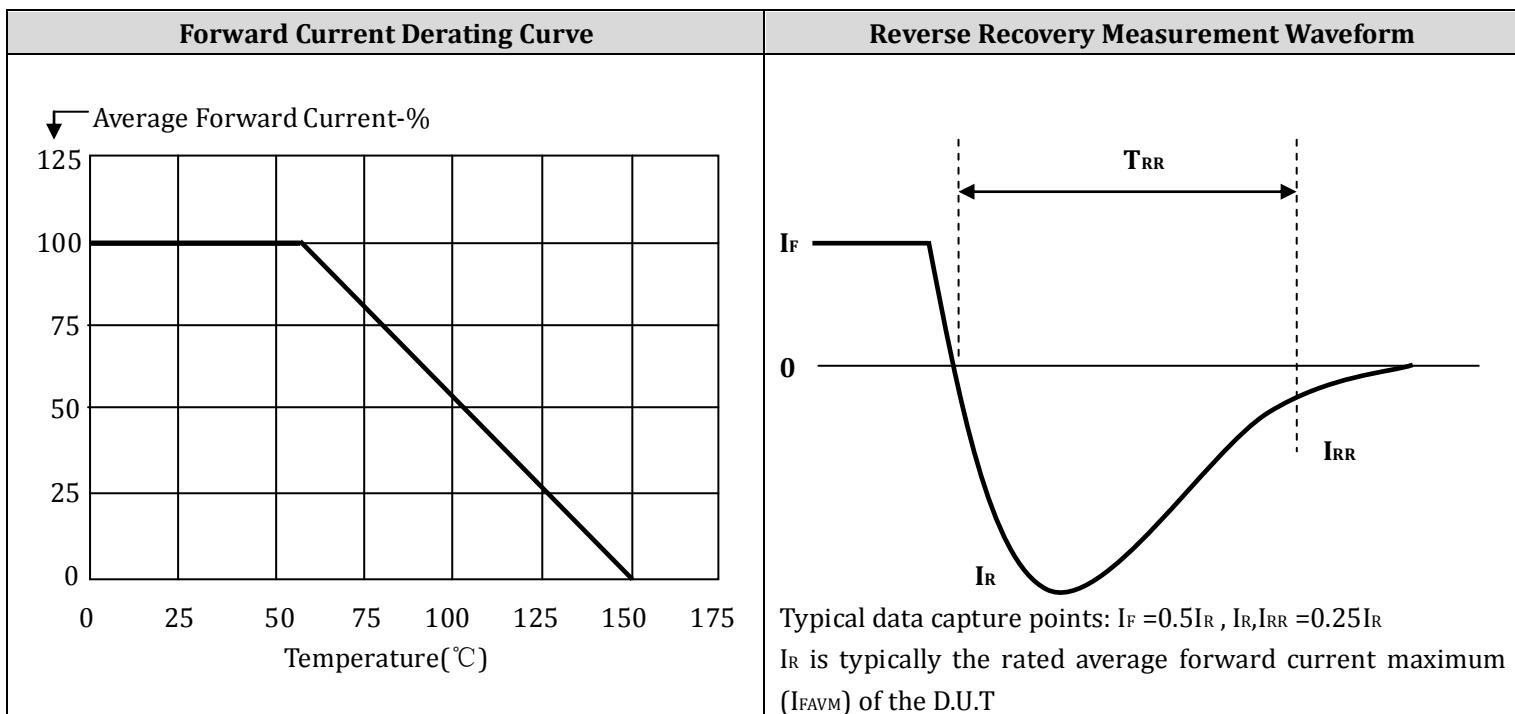
Lead Diameter 1.2mm ±0.02


**MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)**

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	TA=25°C	12	kV
Non-Repetitive Peak Reverse Voltage	V <sub>RSM</sub>	TA=25°C	--	kV
Average Forward Current Maximum	I <sub>FAVM</sub>	TA=55°C	450	mA
		TOIL=55°C	--	mA
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	TA=25°C; 60Hz Half-Sine Wave; 8.3mS	30	A
Junction Temperature	T <sub>J</sub>		150	°C
Allowable Operation Case Temperature	T <sub>C</sub>		-40~+150	°C
Storage Temperature	T <sub>STG</sub>		-40~+150	°C

**ELECTRICAL CHARACTERISTICS: TA=25°C (Unless Otherwise Specified)**

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V <sub>FM</sub>	at 25°C; at I <sub>FAVM</sub>	18	V
Maximum Reverse Current	I <sub>R1</sub>	at 25°C; at V <sub>RRM</sub>	2.0	uA
	I <sub>R2</sub>	at 100°C; at V <sub>RRM</sub>	50	uA
Maximum Reverse Recovery Time	T <sub>RR</sub>	at 25°C; I <sub>F</sub> =0.5I <sub>R</sub> ; I <sub>R</sub> =I <sub>FAVM</sub> ; I <sub>RR</sub> =0.25I <sub>R</sub>	100	nS
Junction Capacitance	C <sub>J</sub>	at 25°C; V <sub>R</sub> =0V; f=1MHz	4.3	pF



Marking	Type	Code	Cathode Mark
	ESJC50F12	ESJC50F12 HVGT	